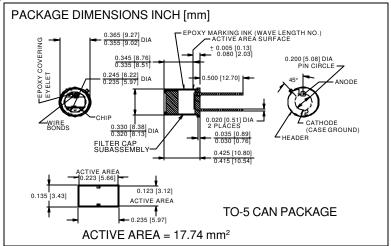
PHOTONIC Silicon Photodiode, Filter Combination Photovoltaic **DETECTORS INC.** (center wavelength 900 nm) Type PDI-V490





RESPONSIVITY (A/W)

FEATURES

- High transmission
- 10⁻⁴ rejection
- +/- 2nm CWL
- Match to GaAlAs LED

DESCRIPTION

The **PDI-V490** is a silicon, PIN planar diffused, photodiode with a wide band interferance filter. The detector filter combination has a wide 50 nm half bandwidth designed for low noise photovoltaic applica-

tions. Packaged in a TO-5 metal can. ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

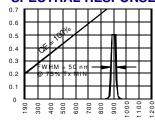
SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		100	V
T _{stg}	Storage Temperature	-20	+85	°C
То	Operating Temperature Range	-15	+70	°C
Ts	Soldering Temperature*		+240	°C
I	Light Current		0.5	mA

^{*1/16} inch from case for 3 secs max

APPLICATIONS

- I.R. sensor
- GaAlAs LED sensor
- Spectrophotometry
- Chemistry instrumentation

SPECTRAL RESPONSE



WAVELENGTH (nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

TA=25 C diffess official foliation (TA=25 C diffess official)									
SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS			
lsc	Short Circuit Current***	H = 100 fc, 2850 K	150	200		μΑ			
ΙD	Dark Current	H = 0, V _R = 10 mV		10	50	pА			
RsH	Shunt Resistance	H = 0, V _R = 10 mV	.20	2		GΩ			
TC Rsh	Rsн Temp. Coefficient	H = 0, V _R = 10 mV		-8		%/℃			
Cı	Junction Capacitance	H = 0, V _R = 10 V**		1700		pF			
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		900		nm			
HBW	Half Bandwidth	(FWHM)		50		nm			
V _{BR}	Breakdown Voltage	I = 10 µuA	50	75		V			
N EP	Noise Equivalent Power	V _R = 10 mV @ Peak		9x10 ⁻¹⁵		W/ √ Hz			
tr	Response Time	RL = 1 KΩ V _R = 10 V		1.0		μS			

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f = 1 MHz, ***without filter